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Atomic switches have recently attracted attention as next-generation nanoswitching devices. They have a simple metal-insulator-metal (MIM) structure and are easily controlled by the formation/decomposition of a conduction filament through the diffusion of active metal ions. Because of a unique switching mechanism based on redox-based electrochemical reactions, these atomic switching devices indicate a low operating voltage ( $<0.05$  V), a high on/off-current ratio ( $>10^6$ ), an exceptionally high retention time ( $>10$  years), and an excellent cyclic endurance ( $>10^6$ ). Because the MIM structure of atomic switches typically consists of active metals (i.e., Cu and Ag), high- $k$  dielectrics (i.e.,  $\text{HfO}_2$ ,  $\text{Al}_2\text{O}_3$ , and  $\text{Ta}_2\text{O}_5$ ), and inactive metals (Pt, W, and TiN), these switching devices can be also formed at low temperatures. Recently, flexible polymer materials are starting to be considered as solid electrolytes for atomic switching devices for future electronic applications.

In this study, we demonstrate a high-performance solid polymer electrolyte (SPE) atomic switching device with low SET/RESET voltages (0.25 and +0.5 V, respectively), high on/off-current ratio ( $10^5$ ), excellent cyclic endurance ( $>10^3$ ), and long retention time ( $>10^4$  s), where poly-4-vinylphenol (PVP)/poly(melamine-co-formaldehyde) (PMF) is used as an SPE layer. This research successfully presents the feasibility of PVP/PMF atomic switches for flexible integrated circuits for next-generation electronic applications.